



SamHop Microelectronics Corp.



STS3414

Ver 1.1

## N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DSON</sub> (mΩ) Max
30V	4A	50 @ V <sub>GS</sub> =10V
		60 @ V <sub>GS</sub> =4.5V
		75 @ V <sub>GS</sub> =2.5V

### FEATURES

- Super high dense cell design for low R<sub>DSON</sub>.
- Rugged and reliable.
- SOT-23 package.



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Limit	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous <sup>a</sup>	4	A
I <sub>DM</sub>	-Pulsed <sup>b</sup>	15	A
P <sub>D</sub>	Maximum Power Dissipation <sup>a</sup>	1.25	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

### THERMAL CHARACTERISTICS

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient <sup>a</sup>	100	°C/W
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## ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V , ID=250uA	30			V
IDSS	Zero Gate Voltage Drain Current	VDS=24V , VGS=0V		1		uA
IGSS	Gate-Body Leakage Current	VGS= ±12V , VDS=0V			±100	nA
<b>ON CHARACTERISTICS</b>						
VGS(th)	Gate Threshold Voltage	VDS=VGS , ID=250uA	0.5	0.9	1.2	V
RDS(ON)	Drain-Source On-State Resistance	VGS=10V , ID=4A		37	50	m ohm
		VGS=4.5V , ID=3A		45	60	m ohm
		VGS=2.5V , ID=1A		50	75	m ohm
gFS	Forward Transconductance	VDS=5.0V , ID=4A		13		S
<b>DYNAMIC CHARACTERISTICS</b> <sup>c</sup>						
Ciss	Input Capacitance	VDS=15V, VGS=0V f=1.0MHz		440		pF
Coss	Output Capacitance			62		pF
CRSS	Reverse Transfer Capacitance			37		pF
<b>SWITCHING CHARACTERISTICS</b> <sup>c</sup>						
tD(ON)	Turn-On Delay Time	VDD=15V ID=1A VGS=10V RGEN=6 ohm		4		ns
tr	Rise Time			8		ns
tD(OFF)	Turn-Off Delay Time			43		ns
tf	Fall Time			5		ns
Qg	Total Gate Charge	VDS=15V, ID=4A, VGS=10V		9.3		nC
		VDS=15V, ID=4A, VGS=4.5V		4.6		nC
Qgs	Gate-Source Charge	VDS=15V, ID=4A, VGS=10V		1		nC
Qgd	Gate-Drain Charge			1.4		nC
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Is	Maximum Continuous Drain-Source Diode Forward Current			1.25		A
VSD	Diode Forward Voltage <sup>b</sup>	VGS=0V, Is=1.25A		0.82	1.2	V
<b>Notes</b>						
a.Surface Mounted on FR4 Board,t ≤ 10sec.						
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.						
c.Guaranteed by design, not subject to production testing.						

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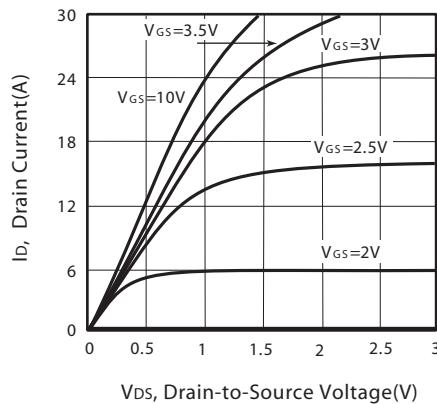


Figure 1. Output Characteristics

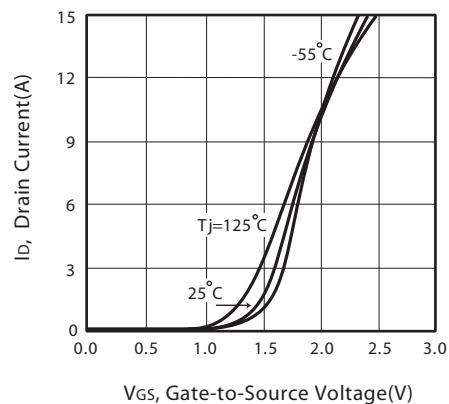


Figure 2. Transfer Characteristics

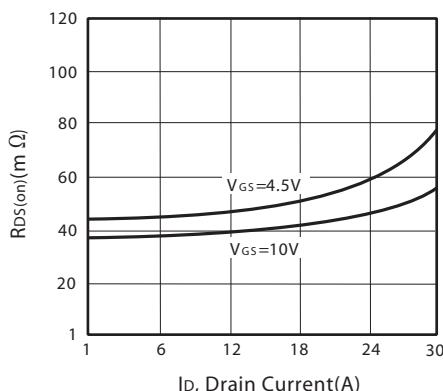


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

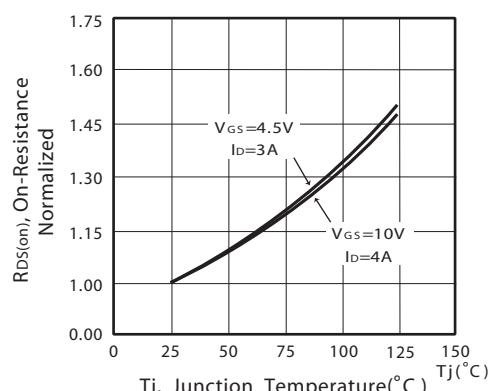


Figure 4. On-Resistance Variation with Drain Current and Temperature

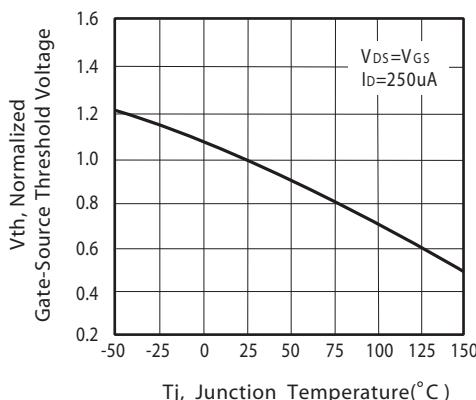


Figure 5. Gate Threshold Variation with Temperature

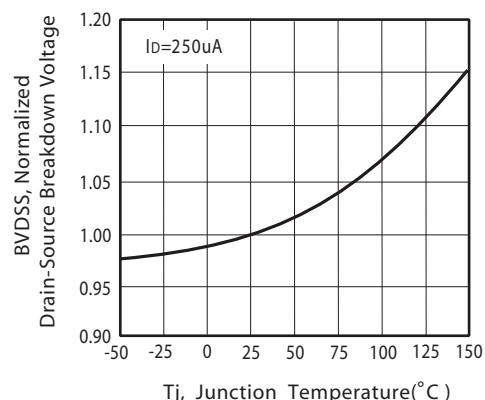
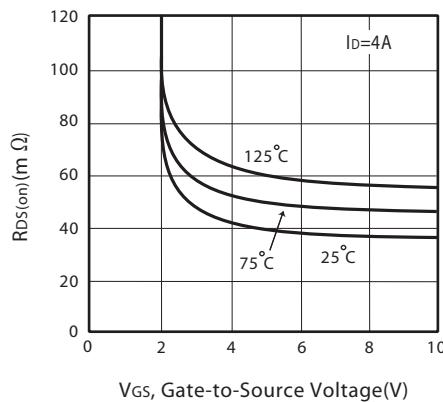


Figure 6. Breakdown Voltage Variation with Temperature

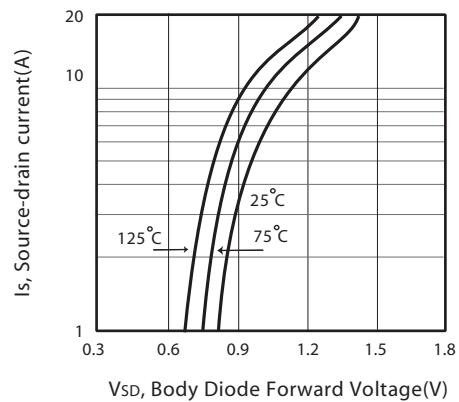
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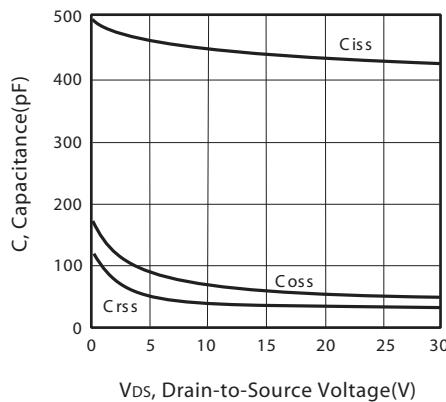
V<sub>GS</sub>, Gate-to-Source Voltage(V)

Figure 7. On-Resistance vs. Gate-Source Voltage



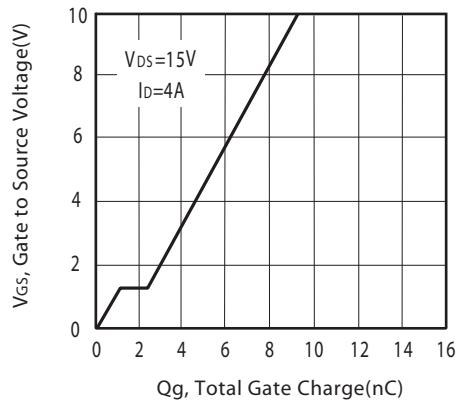
V<sub>SD</sub>, Body Diode Forward Voltage(V)

Figure 8. Body Diode Forward Voltage Variation with Source Current



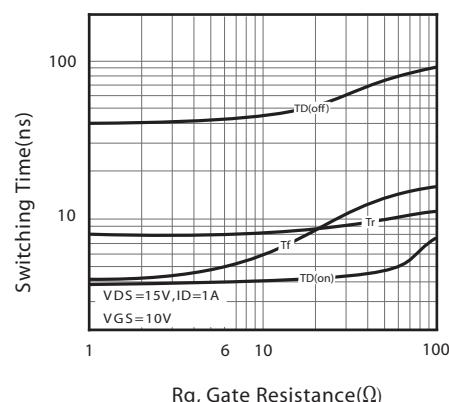
V<sub>DS</sub>, Drain-to-Source Voltage(V)

Figure 9. Capacitance



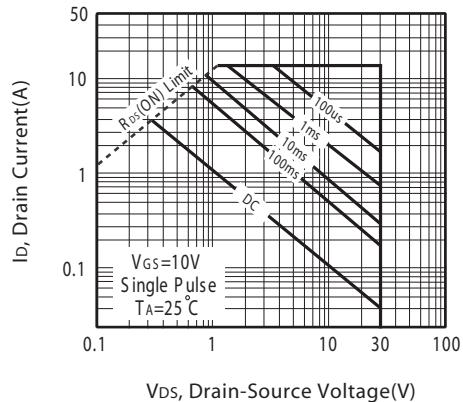
Q<sub>G</sub>, Total Gate Charge(nC)

Figure 10. Gate Charge



R<sub>G</sub>, Gate Resistance(Ω)

Figure 11. switching characteristics



V<sub>DS</sub>, Drain-Source Voltage(V)

Figure 12. Maximum Safe Operating Area

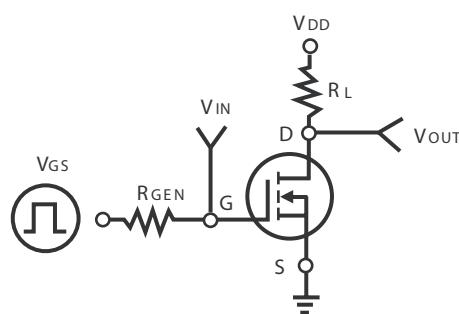


Figure 13. Switching Test Circuit

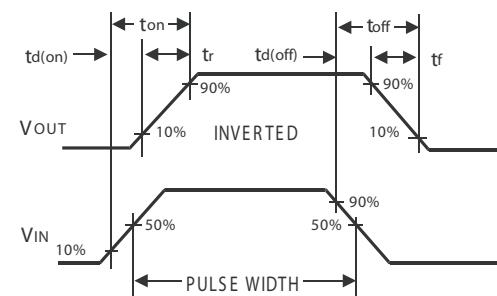
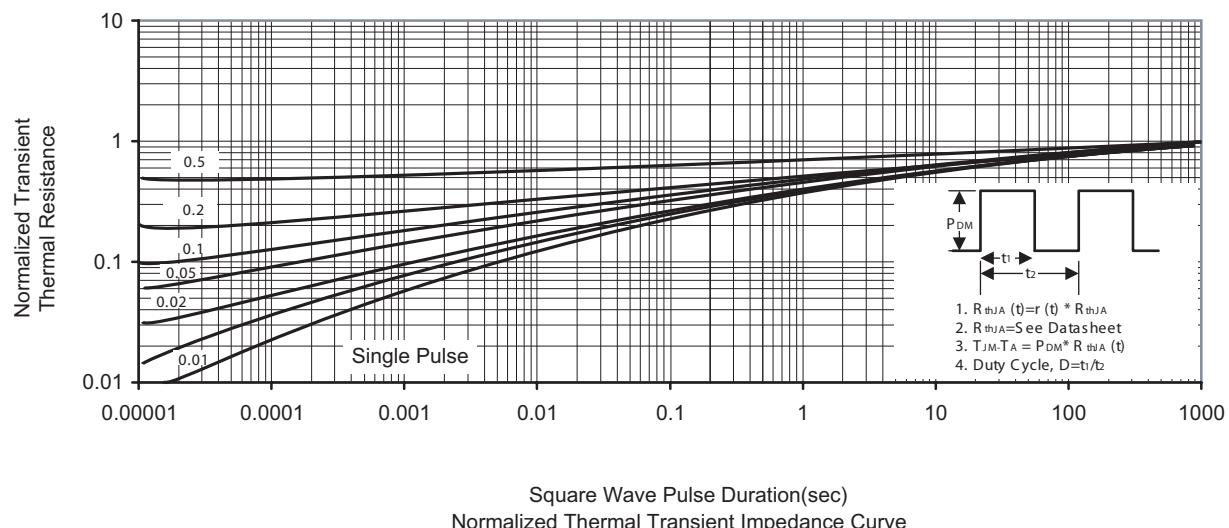
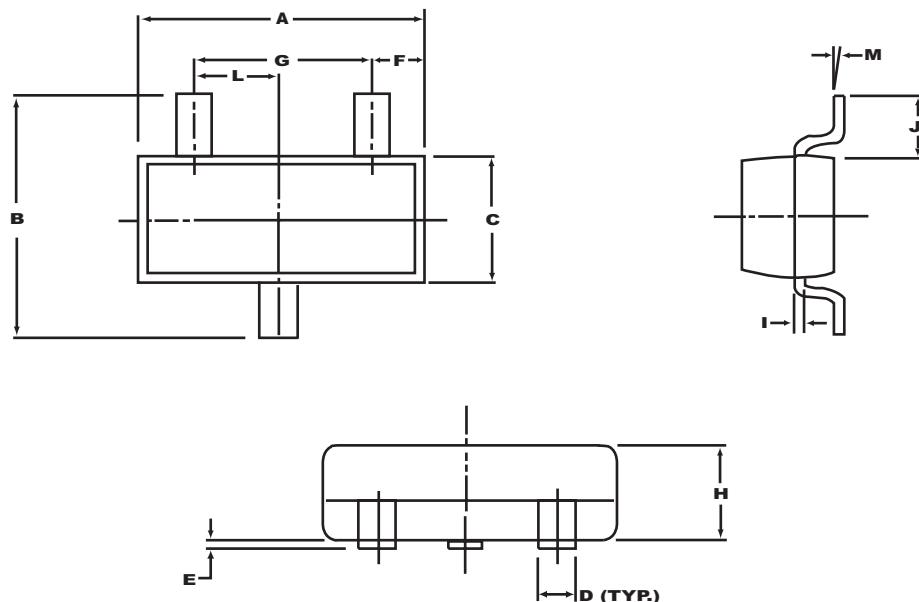


Figure 14. Switching Waveforms



## PACKAGE OUTLINE DIMENSIONS

SOT 23



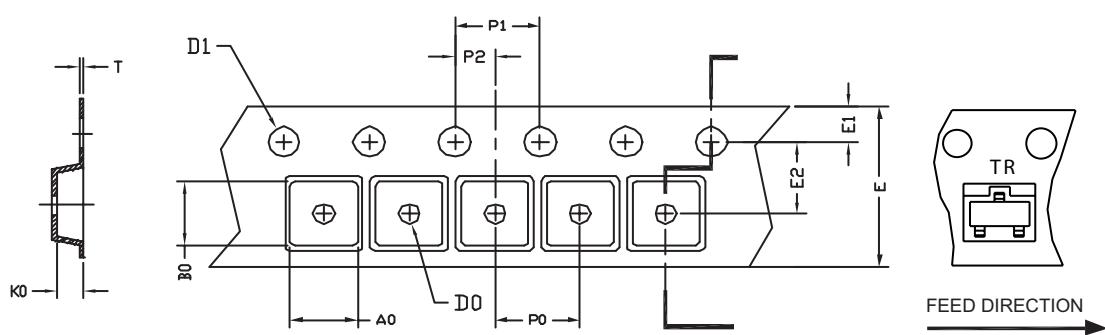
SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.10	0.106	0.122
B	2.40	2.80	0.094	0.110
C	1.40	1.60	0.055	0.063
D	0.35	0.50	0.014	0.020
E	0	0.10	0	0.004
F	0.45	0.55	0.018	0.022
G	1.90 REF.		0.075 REF.	
H	1.00	1.30	0.039	0.051
I	0.10	0.20	0.004	0.008
J	0.40	-	0.016	-
L	0.45	1.15	0.033	0.045
M	0°	10°	0°	10°

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## SOT-23 Tape and Reel Data

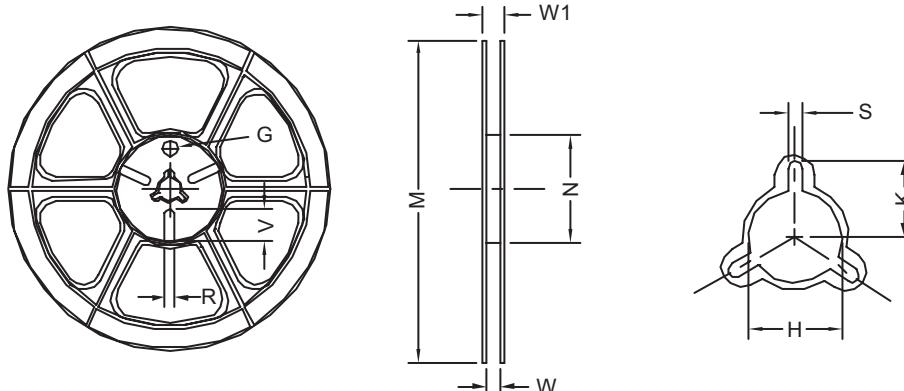
### SOT-23 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23	3.20 ±0.10	3.00 ±0.10	1.33 ±0.10	1.00 +0.25	1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.02

### SOT-23 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	178	178 ±1	60 ±1	9.00 ±0.5	12.00 ±0.5	13.5 ±0.5	10.5	2.00 ±0.5	10.0	5.00	18.00

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